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NTE158
Germanium PNP Transistor
Audio Power Amplifier

Description:

The NTE158 is a germanium PNP triode transistor in a TO1 type package designed for low–power, large signal audio applications.

Absolute Maximum Ratings: (T_A = +25°C)

Collector–Base Voltage, V_{CBO} 32V

Collector–Emitter Voltage ($R_{BE} \le 500\pm$), V_{CER} 32V

Emitter–Base Voltage, V_{EBO} 10V

Collector Current, I_C 1A

Base Current, I_B 40mA

Power Dissipation (T_A = +25°C), P_C 550mW

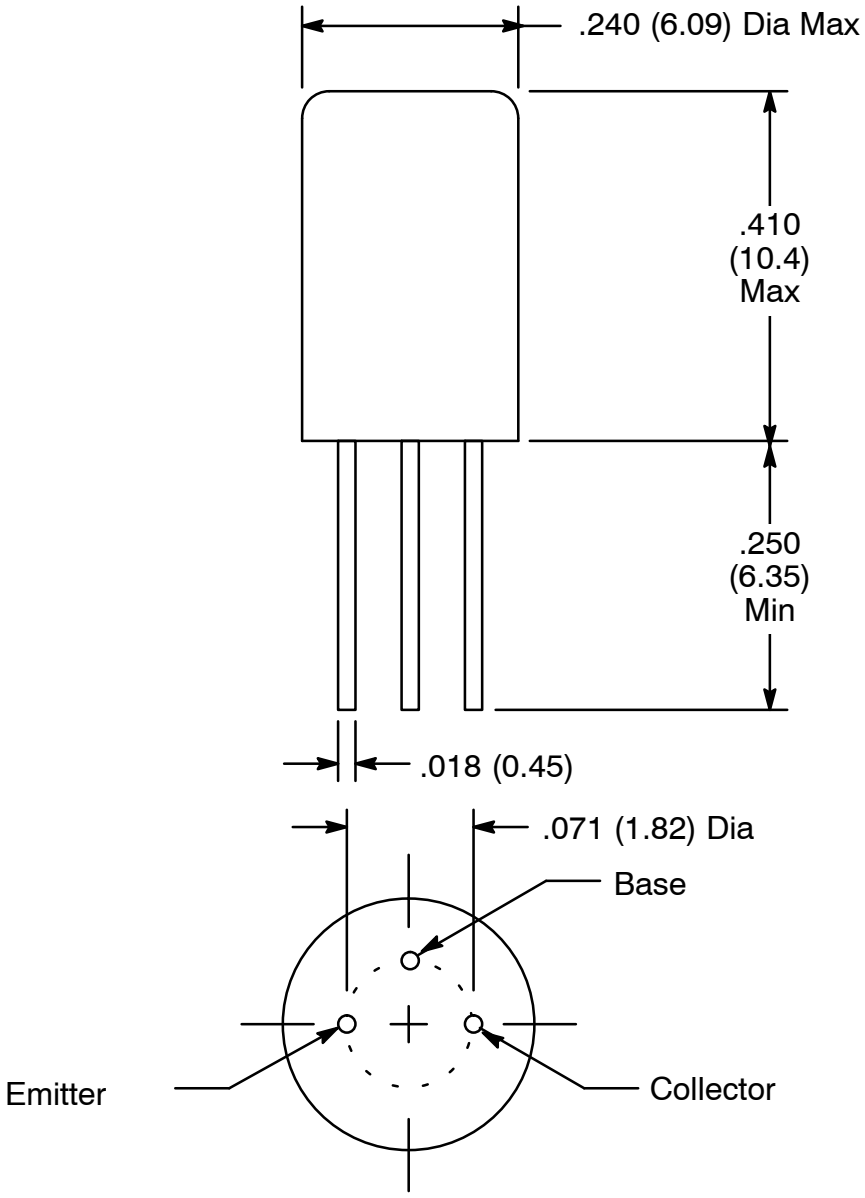
Derate Above 25°C . . . . . 0.3mW/°C

Storage Temperature Range, T_{stg} . . . . . –55° to +90°C

Lead Temperature (During Soldering, 1/16” ±1/32” from case for 5sec), T_L . . . . . +245°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 200≤A, I_E = 0	32	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 200≤A, I_C = 0	10	–	–	V
Collector Cutoff Current	I_{CBO}	V_{CB} = –10V, I_E = 0	–	–	10	≤A
Emitter Cutoff Current	I_{EBO}	V_{EB} = –5V, T_J = +75°C	–	–	500	≤A
DC Current Gain	h_{FE}	V_{CB} = 1V, I_C = 300mA	50	90	175	
Base–Emitter Voltage	V_{BE}	V_{CE} = 1V, I_C = 300mA	280	–	600	mV
Forward Current Transfer Cutoff Frequency	f_{hfe}		10	–	20	kc
Output Capacitance	C_{ob}	V_{CB} = –5V, I_E = 0 @ 0.45mc	80	–	105	pF


.240 (6.09) Dia Max
.410
(10.4)
Max
.250
(6.35)
Min
.018 (0.45)
.071 (1.82) Dia
Base
Emitter
Collector